

High Voltage IGBT with Diode

IXGX 32N170H1



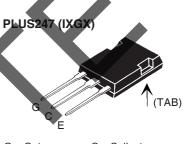
G C E	
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Symbol	Test Conditions	Maximum Ra	Maximum Ratings			
V _{CES}	$T_J = 25^{\circ}C \text{ to } 150^{\circ}C$	1700	V			
V _{CGR}	$T_{_{ m J}}$ = 25°C to 150°C; $R_{_{ m GE}}$ = 1 M Ω	1700	V			
V _{GES}	Continuous	±20	V			
\mathbf{V}_{GEM}	Transient	±30	V			
I _{C25}	T _c = 25°C	75	A			
I _{C90}	$T_{c} = 90^{\circ}C$	32	A			
I _{CM}	$T_{\rm C}$ = 25°C, 1 ms	200	А			
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_{G} = 5 Ω Clamped inductive load	I _{CM} = 90 @ 0.8 V _{CES}	A			
t _{sc}	$T_J = 125^{\circ}C, V_{CE} = 1200 \text{ V}; V_{GE} = 15 \text{ V}, R_{GE}$	=10Ω 10	μs			
P _c	T _C = 25°C	350	W			
T_{J}		-5 5 +150	°C			
T_{JM}		150	°C			
T _{stg}		-55 +150	°C			
F _c	Mounting force with chip	22130/530	N/lb			
	ead temperature for soldering 062 in.) from case for 10 s	300	°C			
Weight		6	g			

Symbol Test Conditions	Cha	racter	istic Values
	$(T_{\perp} = 25^{\circ}C, \text{ unless of})$	herwi	se specified)
	min.	typ.	max.

			typ.	IIIax.	
BV _{CES}	$I_{C} = 1 \text{mA}, V_{GE} = 0 \text{ V}$ $I_{C} = 250 \mu\text{A}, V_{CE} = V_{GE}$	1700 3.0		5.0	V
I _{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 V$ No	$T_{J} = 25^{\circ}C$ te 1 $T_{J} = 125^{\circ}C$		500 8	μA mA
I _{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			±100	nA
V _{CE(sat)}	$I_{\rm C} = I_{\rm C90}, V_{\rm GE} = 15 \rm V$	$T_J = 25^{\circ}C$ $T_J = 125^{\circ}C$	2.5 3.0	3.3	V

= 1700 **V**_{CES} **75** 290 ns $\boldsymbol{t}_{\text{fi(typ)}}$



G = Gate. Emitter,

C = Collector, TAB = Collector

Features

- High current handling capability
- MOS Gate turn-on
 - drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies



Symbol	Test Conditions Characteristic Values $(T_J = 25^{\circ}C, \text{ unless otherwise specified } $ min. typ. max.		
g _{fs}	I _C = I _{C25} ; V _{CE} = 10 V 25 Note 2	33	S
C _{ies} C _{oes} C _{res}	$ V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz} $	3500 250 40	pF pF pF
$egin{array}{c} oldsymbol{Q}_{g} \ oldsymbol{Q}_{ge} \ oldsymbol{Q}_{gc} \end{array}$		155 30 51	nC nC nC
$\mathbf{t}_{ ext{d(on)}}$ $\mathbf{t}_{ ext{ri}}$ $\mathbf{t}_{ ext{d(off)}}$ $\mathbf{t}_{ ext{fi}}$ $\mathbf{E}_{ ext{off}}$	Inductive load, $T_J = 25^{\circ}C$ $\begin{vmatrix} I_C = I_{C90}, V_{GE} = 15 \text{ V} \\ R_G = 2.7 \Omega, V_{CE} = 0.8 V_{CES} \\ \text{Note 3} \end{vmatrix}$	45 38 270 250 15	ns ns 500 ns 500 ns 25 mJ
$t_{d(on)}$ t_{ri} E_{on} $t_{d(off)}$ t_{fi} E_{off} R_{thJC} R_{thCK}	Inductive load, $T_J = 125^{\circ}C$ $I_C = I_{C90}, V_{GE} = 15 \text{ V}$ $R_G = 2.7 \Omega, V_{CE} = 0.8 \text{ V}_{CES}$ Note 3	48 42 6.0 360 560 22	ns ns md ns ns mJ

F	PLUS247 Outline (IXGX)					
L	SYM	INCH			1E TERS	
И		MIN	MAX	MIN	MAX	
T,	A	190	.205	4.83	5.21	
	A1	.090	.100	2.29	2.54	
1	A2	075	.085	1.91	2.16	
1	b - 1	.045	.055	1.14	1.40	
1	b1 b2	.075	.084	1.91	2.13	
L		.115	.123	2.92	3.12	
и	C	.024	.031	0.61	0.80	
17	D	.819	.840	20.80	21.34	
	E	.620	.635	15.75	16.13	
1	e	.215		5.45		
1	L_	.780	.800	19.81	20.32	
		.150	.170	3.81	4.32	
Ν.	<u>Q</u>	.220	.244	5.59	6.20	
M	R	.170	.190	4.32	4.83	
	S	.520	.540	13.21	13.72	
	T	.620	.640	15.75	16.26	
1	U	.065	.080	1.65	2.03	
1 - GATE 2 - DRAIN (COLLECTOR) 3 - SOURCE (EMITTER) 4 - NO CONNECTION NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.						

Reverse Diode (FRED) (Note 4)

Characteristic Values

25°C (inless otherwise specified)

Symbol	Test Conditions min.	therwis typ.	se specified) max.
V _F	$I_F = 70A$, $V_{GE} = 0$ V, Pulse test, $t \le 200$ µs, duty cycle $d \le 2$ %		2.7 V
$\left\{ egin{array}{l} \mathbf{I}_{RM} \\ \mathbf{t}_{rr} \end{array} ight. ight.$	$I_{\mu} = 50A$, $V_{GE} = 0 V$, $-di_{F}/dt = 800 A/\mu s$ $V_{R} = 600 V$	50 150	A ns
R _{thJC}			0.4 K/W

- Notes: 1. Device must be heatsunk for high temperature leakage current measurements to avoid thermal runaway.
 - 2. Pulse test, $t \le 300 \ \mu s$, duty cycle $\le 2 \ \%$
 - 3. Switching times may increase for $V_{\rm CE}$ (Clamp) > 0.8 $V_{\rm CES}$, higher T $_{\rm J}$ or increased R $_{\rm G}$.
 - See DH60-18A and IXGH32N170A datasheets for additional characteristics

IXYS reserves the right to change limits, test conditions, and dimensions.

